

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- ► Low threshold (2.0V max.)
- ▶ High input impedance and high gain
- ▶ Free from secondary breakdown
- ► Low C_{ISS} and fast switching speeds

Applications

- ▶ Logic level interfaces ideal for TTL and CMOS
- Solid state relays
- ▶ Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device		Package Options	BV _{DSS} /BV _{DGS}	R _{DS(ON)}	D(ON)	$V_{GS(th)}$	
	TO-236AB (SOT-23)	TO-92	TO-243AA (SOT-89)		(max) (Ω)	(min) (A)	(max) (V)
TN5325	TN5325K1-G	TN5325N3-G	TN5325N8-G	250	7.0	1.2	2.0

⁻G indicates package is RoHS compliant ('Green')



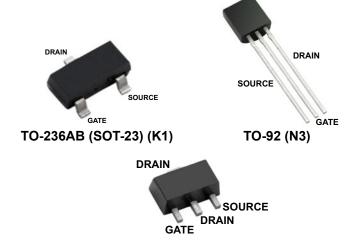


Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV _{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configurations



TO-243AA (SOT-89) (N8)

Product Marking

N3CW

W = Code for week sealed
_____ = "Green" Packaging

TO-236AB (SOT-23) (K1)

SiTN
5 3 2 5
WW = Year Sealed
WW = Week Sealed
Green" Packaging

TO-92 (N3)

TN3CW W = Code for week sealed _____ = "Green" Packaging

TO-243AA (SOT-89) (N8)

Packages may or may not include the following marks: Si or

^{*} Distance of 1.6mm from case for 10 seconds.

Thermal Characteristics

Package	I _D (continuous) [†] (mA)	I _D (pulsed) (A)	Power Dissipation @T _A = 25°C (W)	θ _{jc} (°C/W)	θ _{ja} (°C/W)	I _{DR} [†] (mA)	I _{DRM} (A)
TO-236AB (SOT-23)	150	0.4	0.36	200	350	150	0.4
TO-92	215	0.8	0.74	125	170	215	0.8
TO-243AA (SOT-89)	316	1.5	1.6 [‡]	15	78 [‡]	316	1.5

Notes:

Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions		
BV _{DSS}	Drain-to-source breakdown voltage	250	-	-	V	$V_{GS} = 0V, I_{D} = 100 \mu A$		
$V_{\rm GS(th)}$	Gate threshold voltage	0.6	-	2.0	V	$V_{GS} = V_{DS}$, $I_{D} = 1.0$ mA		
$\Delta V_{GS(th)}$	Change in V _{GS(th)} with temperature	-	-	-4.5	mV/°C	$V_{GS} = V_{DS}$, $I_{D} = 1.0$ mA		
I _{GSS}	Gate body leakage	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
		-	-	1.0	μA	$V_{GS} = 0V, V_{DS} = 100V$		
I _{DSS}	Zero gate voltage drain current	-	-	10	μA	$V_{GS} = 0V, V_{DS} = Max Rating$		
DSS		-	-	1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$, $T_A = 125$ °C		
	On-state drain current	0.6	-	-	A	$V_{GS} = 4.5V, V_{DS} = 25V$		
I _{D(ON)}	On-state drain current	1.2	_	-	A	V _{GS} = 10V, V _{DS} = 25V		
В	Static drain-to-source	-	_	8.0	Ω	V _{GS} = 4.5V, I _D = 150mA		
R _{DS(ON)}	on-state resistance	-	_	7.0	12	V _{GS} = 10V, I _D = 1.0A		
$\Delta R_{DS(ON)}$	Change in R _{DS(ON)} with temperature	-	_	1.0	%/°C	V _{GS} = 4.5V, I _D = 150mA		
G_{FS}	Forward transductance	150	-	-	mmho	$V_{DS} = 25V, I_{D} = 200mA$		
C _{ISS}	Input capacitance	-	-	110		V = 0V.		
C _{oss}	Common source output capacitance	-	-	60	pF	$V_{GS} = 0V,$ $V_{DS} = 25V,$		
C _{RSS}	Reverse transfer capacitance	-	_	23		f = 1.0MHz		
t _{d(ON)}	Turn-on delay time	-	_	20				
t _r	Rise time Turn-off delay time		-	15	no	V _{DD} = 25V,		
t _{d(OFF)}			-	25	ns	$I_D = 150 \text{mA},$ $R_{GEN} = 25\Omega$		
t _f	Fall time	-	-	25		GLIN		
V _{SD}	Diode forward voltage drop	-	-	1.8	V	V _{GS} = 0V, I _{SD} = 200mA		
t _{rr}	Reverse recovery time	-	300	-	ns	V _{GS} = 0V, I _{SD} = 200mA		

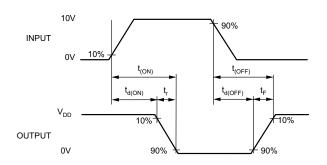
Notes:

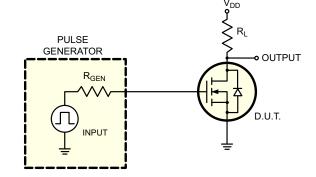
[†] I_D (continuous) is limited by max rated T_j . ‡ Mounted on FR5 Board, 25mm x 25mm x 1.57mm.

^{1.} All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

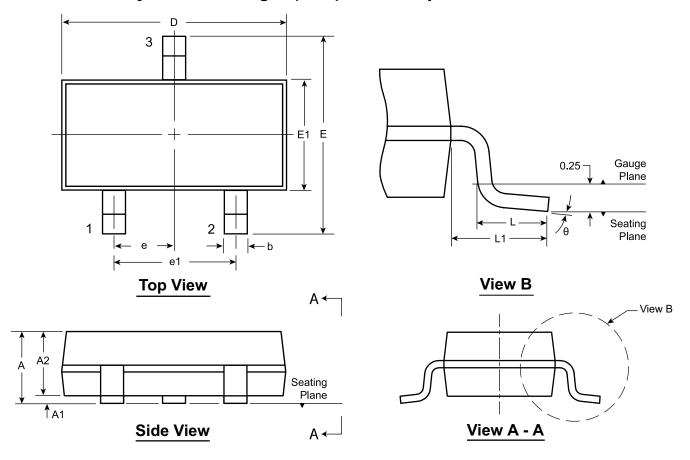
^{2.} All A.C. parameters sample tested.

Switching Waveforms and Test Circuit





3-Lead TO-236AB (SOT-23) Package Outline (K1) 2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



Symbol		Α	A1	A2	b	D	E	E1	е	e1	L	L1	θ
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.05	4.00	0.20 [†]	0.54	0 °
	NOM	-	_	0.95	-	2.90	-	1.30	0.95 BSC		0.50	0.54 REF	-
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40	1000		530	D3C	0.60

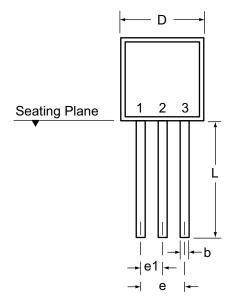
JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

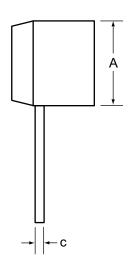
Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

[†] This dimension differs from the JEDEC drawing.

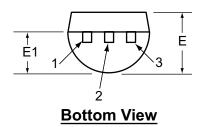
3-Lead TO-92 Package Outline (N3)





Front View

Side View



Symbol		Α	b	С	D	E	E1	е	e1	L
Dimensions (inches)	MIN	.170	.014 [†]	.014 [†]	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022 [†]	.022 [†]	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

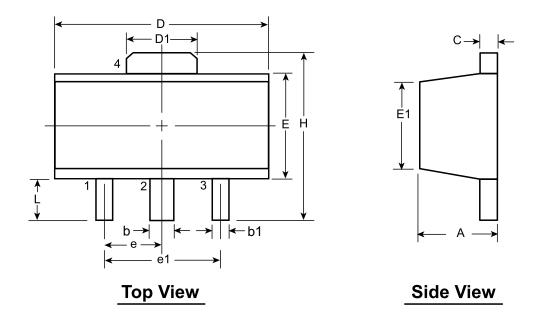
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Supertex Doc.#: DSPD-3TO92N3, Version E041009.

^{*} This dimension is not specified in the JEDEC drawing.

[†] This dimension differs from the JEDEC drawing.

3-Lead TO-243AA (SOT-89) Package Outline (N8)



Symbol		Α	b	b1	С	D	D1	Е	E1	е	e1	Н	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.00 [†]	1.50 BSC		3.94	0.89
	NOM	-	-	-	-	-	-	-	-			-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

† This dimension differs from the JEDEC drawing

Drawings not to scale.

Supertex Doc. #: DSPD-3TO243AAN8, Version E051509.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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